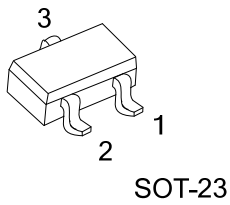
N-CHANNEL ENHANCEMENT MODE MOSFET

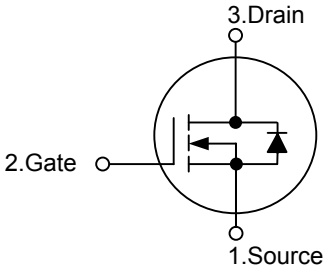


■ DESCRIPTION

The **UT3404** is N-Channel enhancement mode power MOSFET, designed with high density cell, with fast switching speed, low on-resistance, excellent thermal and electrical capabilities and operation with low gate voltages.

This device is suitable for use as a load switch or in PWM applications.

■ SYMBOL

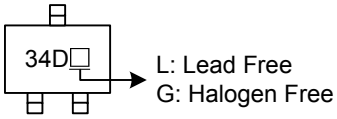


■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT3404L-AE3-R	UT3404G-AE3-R	SOT-23	S	G	D	Tape Reel

UT3404L-AE3-R (1)Packing Type (2)Package Type (3)Lead Plating	(1) R: Tape Reel (2) AE3: SOT-23 (3) G: Halogen Free, L: Lead Free

■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_A = 25℃, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (Note 3)	I_D	5.8	A
Pulsed Drain Current (Note 1, 2)	I_{DM}	20	A
Power Dissipation	P_D	1.4	W
Junction Temperature	T_J	+150	℃
Strong Temperature	T_{STG}	-55 ~ +150	℃

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

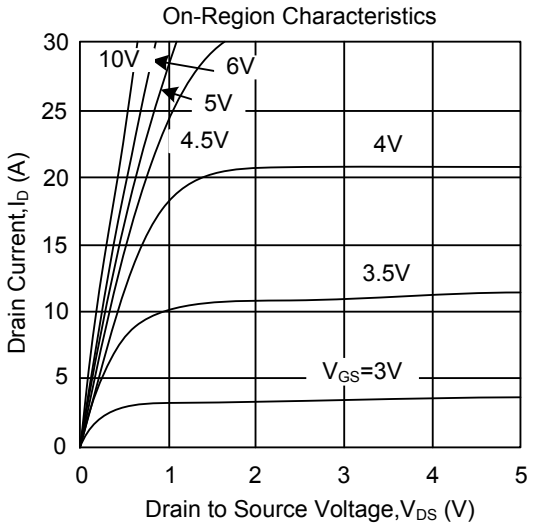
PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction to Ambient (Note 3)	θ_{JA}		85	125	℃/W

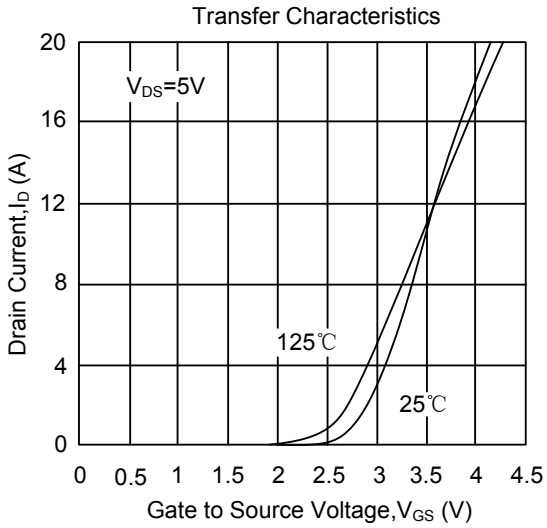
■ ELECTRICAL CHARACTERISTICS (T_J=25℃, unless otherwise specified)

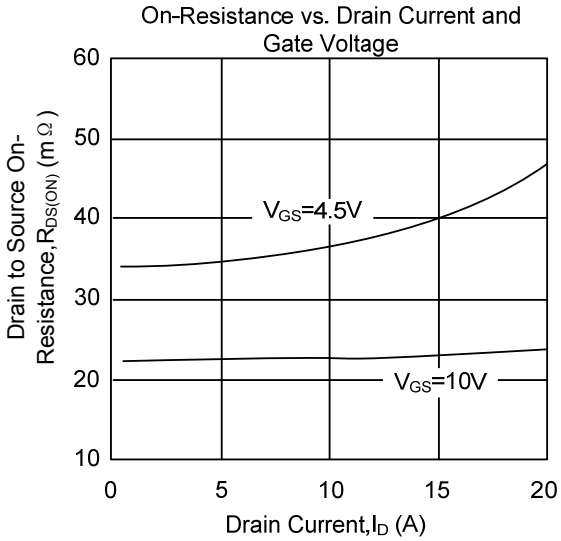
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	30			V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=24V, V_{GS}=0V			1	uA
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250uA	1	1.9	3	V
On State Drain Current	$I_{D(ON)}$	V_{GS}=4.5V, V_{DS}=5V	20			A
Drain-Source On-State Resistance (Note 2)	$R_{DS(ON)}$	V_{GS}=10V, I_D=5.8A		22.5	28	mΩ
		V_{GS}=4.5V, I_D=5A		34.5	43	mΩ
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	V_{GS}=0V,V_{DS}=15V, f=1.0MHz		680	820	pF
Output Capacitance	C_{OSS}			102		pF
Reverse Transfer Capacitance	C_{RSS}			77		pF
SWITCHING CHARACTERISTICS						
Turn-ON Delay Time (Note 2)	$t_{D(ON)}$	V_{DS}=15V, V_{GS}=10V, R_G=3Ω, R_D=2.7Ω		4.6	6.5	ns
Turn-ON Rise Time	t_R			3.8	5.7	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			20.9	30	ns
Turn-OFF Fall Time	t_F			5	7.5	ns
Total Gate Charge (Note 2)	Q_G	V_{DS}=15V, V_{GS}=10V, I_D=5.8A		13.88	17	nC
Gate-Source Charge	Q_{GS}			1.8		nC
Gate-Drain Charge	Q_{GD}			3.12		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage(Note2)	V_{SD}	I_S=1A		0.76	1	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				2.5	A
Reverse Recovery Time	t_{RR}	I_F=5.8A, dI/dt=100A/μs		16.1	21	ns
Reverse Recovery Charge	Q_{RR}			7.4	10	nC

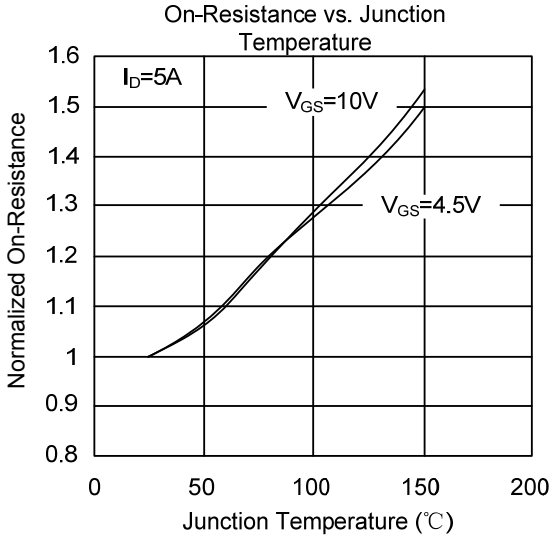
Notes: 1. Pulse width limited by $T_{J(MAX)}$
2. Pulse width ≤300us, duty cycle ≤2%.
3. Surface mounted on 1 in^2 copper pad of FR4 board.

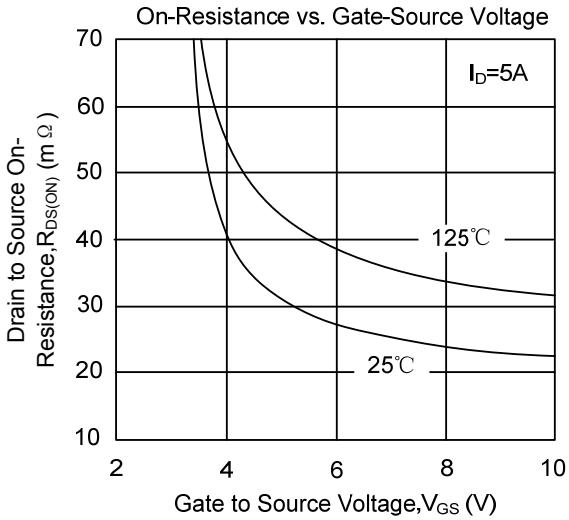
■ TYPICAL CHARACTERISTICS

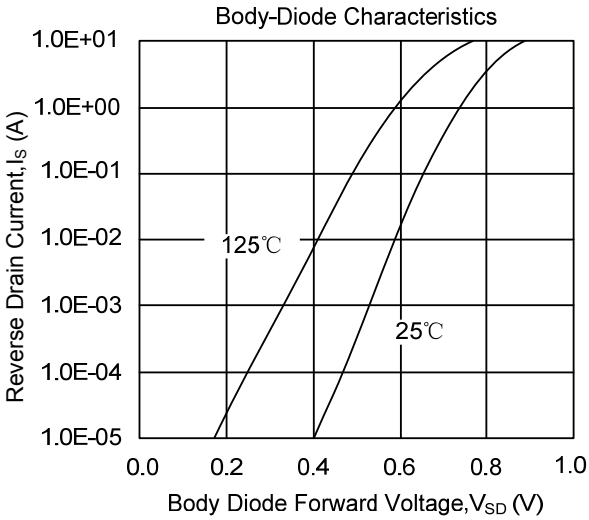




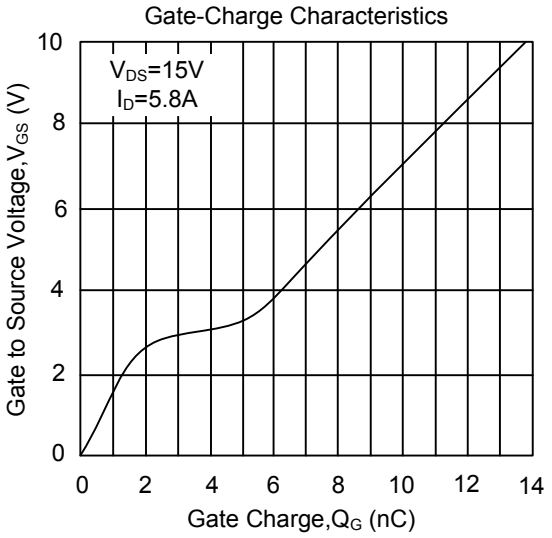


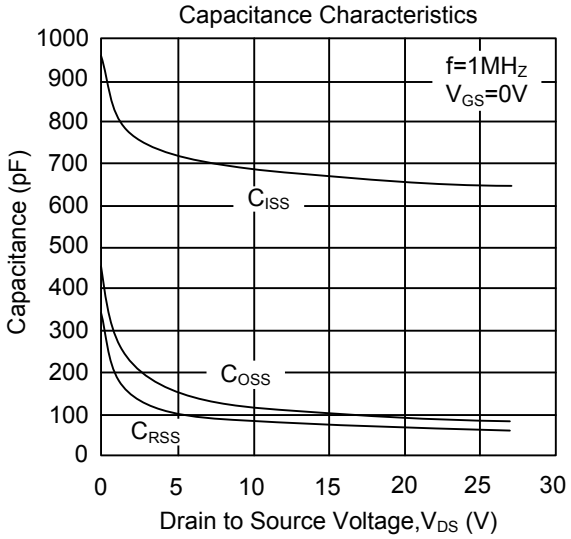


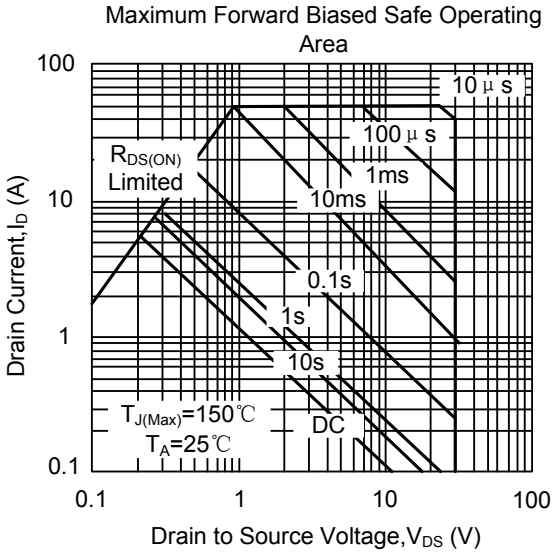


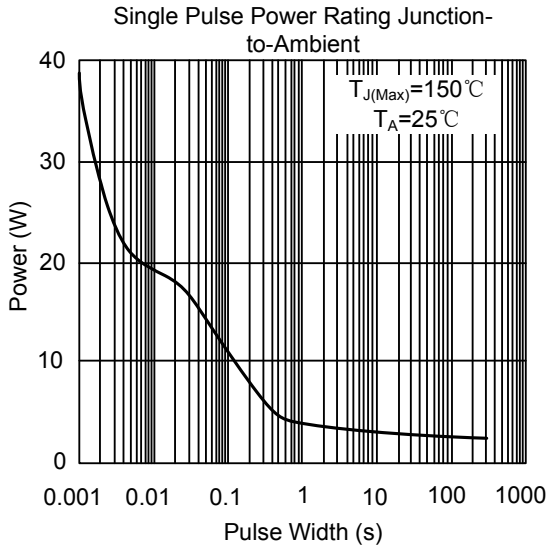


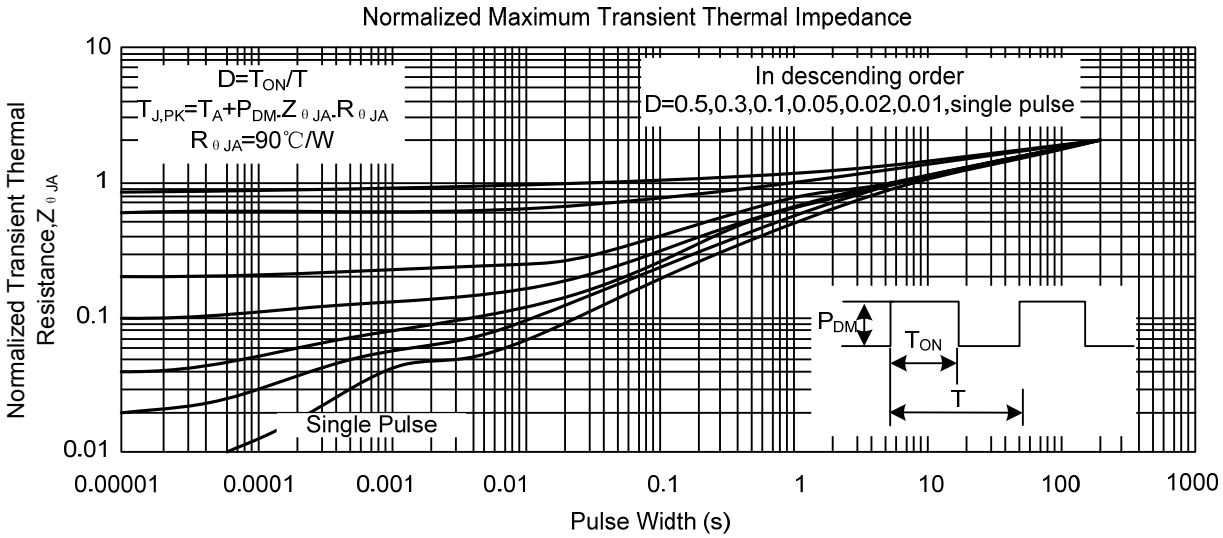
■ TYPICAL CHARACTERISTICS(Cont.)











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